Andreev and Josephson Transport in InAs Nanowire-based Quantum Dots

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Motivation

- One-dimensional Topological Superconductors have seen recent attention because:
- They host a pair of Majorana Bound States (MBS) at the ends of a quantum wire, which are **chargeless**, **spinless**, and at **zero energy**.
- A recipe for MBS: a superconductor / semiconducting nanowire / superconductor proximity effect junction, in a strong magnetic field. [R. Lutchyn et al., PRL 105, 077001 (2010)]
- InAs nanowires are suitable as the semiconductor (strong spin-orbit coupling), and Nb as the superconductor (high critical field).



- A <u>quantum dot</u> embedded in the semiconductor can be used to perform initialization and readout operations on the MBS.
 [K. Flensberg, PRL **106**, 090503 (2011)]
- [J. Alicea et al., Nature Physics **7**, 412–417 (2011)]

Proximity Effect in Quantum Dots Coupled to Superconductors



Anderson Impurity Model

- Minimal Model for a Quantum Dot connected to a S.C. bank.
- A pair of Andreev Bound States (ABS) predicted, shown below for U >> Δ.
- The coupling strength Γ qualitatively changes the behaviour of ABS vs. dot energy.



Nb-InAs nanowire-Nb Field Effect Transistor Devices



• Theory: KG, J. Baugh arXiv:1411.3054

• Experiment: KG, G.W. Holloway, J. Baugh et al., arXiv:1405.7455

- Some devices can be tuned to the Josephson Transport regime.
- I_c up to 55 nA observed.
- Orbital Josephson Interference observed in an axial magnetic field.



Nb-InAs naowire-Nb Field Effect Transistor Devices



 $dI/dV(2e^2/h)$ 0.005 0.004 4 0.004 0.003 0.003 V(mV)0.002 0 0.002 -20.001 0.001 -40.000 0.000 0.1 0.2 0.3 0.4 0.5 0.6 V_q (V) Device 2

We concentrate on devices tuned to the quantum dot regime.

- Charging Energy U ~ 10 meV
- μ (20 K) > 5000 cm²/(V.s)
- Signatures of Andreev transport observed within the bias window $-\Delta/e$ to Δ/e .
- Δ = 1.1 meV



Andreev Transport in Nb-InAs nanowire-Nb Devices $dI/dV(2e^2/h)$





Features above and below the ABS might be:

- Another pair of ABS, connected to the continuum levels.
- Signatures of Multiple Andreev Reflection, rounded near the charge degeneracy points.

Splitting in a Magnetic Field



- The ABS are split in the presence of an axial magnetic field.
- A Landé factor of $g \, \approx \, 8$ is estimated from the maximum splitting.
- Splitting appears for every other charge state (even-odd effect), consistent with the Anderson model.
- The splitting closes as V_{g} moves away from the charge degeneracy point.
 - The nature of the ground-state is changing why?

Other Andreev Bound States



- More complex features visible as the devices are tuned to more conductive regimes.
- ABS appear to be pinned to zero energy to form a zero-bias peak.

• Two pairs of ABS visible, which might indicate two dots in series.

Conclusions

- Proximity superconductivity observed in Nb-InAs nanowire-Nb junction devices tuned to the Intermediate Coupling regime, with $\Gamma \sim \Delta \ll U$.
- Similar devices can be used to look for signatures of Majorana Bound States in Topological Superconductors.
- Rich and complex Andreev transport features go beyond the Anderson impurity model, especially when devices are tuned to more conductive regimes.

local bottom gates

- Future work will look at Andreev transport features in different geometries, including: -
 - SQUIDs, so the junction can be phase-biased.
 - Devices with local bottom gates, so Γ can be tuned.







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